Abstract of the Disclosure

A method of manufacturing a semiconductor device comprises; forming a device isolation region in a semiconductor substrate; forming at least a first conductivity type impurity region in the semiconductor substrate; and forming on the semiconductor substrate a transistor including a gate insulating film, a gate electrode, source/drain regions and a channel located directly under the gate electrode, wherein the first conductivity type impurity region is formed by the steps of: an ion implantation 1 having a concentration peak at a location deeper than the bottom of the device isolation region; an ion implantation 2 having a concentration peak at a location around the bottom of the device isolation region; an ion implantation 3 having a concentration peak around the junction regions where the source/drain regions are to be formed; and an ion implantation 4 having a concentration peak on the surface or directly under the surface of the region where the channel is to be formed.

This Sheet Has Been Replaced